

DESCRIPTIVE ABSTRACT

The invention relates to the field of fabrication methods in thin layers, for example of 5 integrated electronic circuits or MEMS.

It relates to a correction method allowing design errors made for example by photolithography in a thin layer to be repaired, and without necessarily having to utilise a new mask or without having to 10 correct an erroneous mask. The invention likewise comprises a lithography device allowing certain of the steps of such a method to be employed.

Figure 3A.